

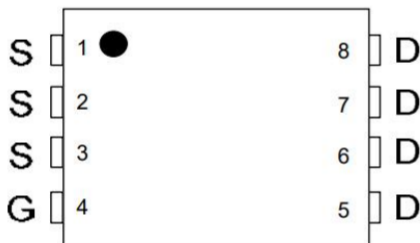
Product Summary

- V_{DS} 150 V
- I_{DS} (at $V_{GS}=10V$) 50A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $\leq 13m\Omega$ (TYP)

Application

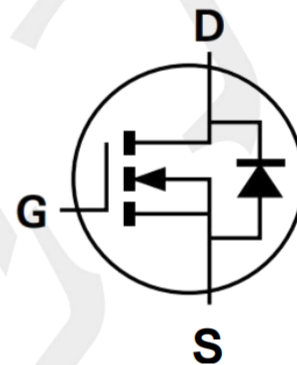
- Load switch
- High Frequency Switching and Synchronous Rectification
- Active Clamp in Intermediate
- DC/DC Power Supplies

Package and Pin Configuration



PDFN5X6-8

Circuit diagram



Absolute Maximum Ratings

($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ C$	50
		$T_C=100^\circ C$	35
Pulsed Drain Current	I_{DM}	200	A
Single Pulse Avalanche Energy	EAS	306	mJ
Total Power Dissipation	P_{DTOT}	120	W
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ C$

Thermal Characteristic

PARAMETER	Symbol	Value	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	50	$^\circ C/W$
Thermal Resistance Junction-Case	$R_{\theta JC}$	1.04	$^\circ C/W$

Note : The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.

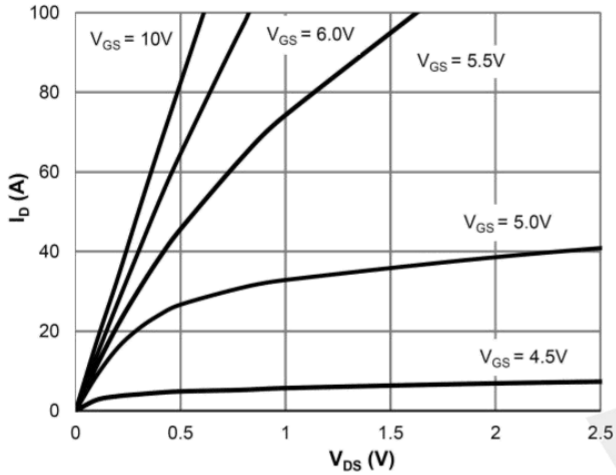
Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	BV _{DSS}	145	150	--	V
Gate-Source Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	V _{GS(th)}	2.0	--	4.0	V
Gate-Source Leakage	V _{DS} =0V, V _{GS} =±20V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} =90V, V _{GS} =0V	I _{DSS}	--	0.1	1.0	μA
	V _{DS} =90V, T _J =55°C		--	1.0	5.0	μA
Drain-Source On-State Resistance (Note 1)	V _{GS} =10V, I _D =20A	R _{DS(on)}	--	13	16	mΩ
Dynamic (Note 2)						
Total Gate Charge (Note 3)	V _{DS} =75V, I _D =20A, V _{GS} =10V	Q _g	--	30	--	nC
Gate-Source Charge (Note 3)		Q _{gs}	--	5.8	--	
Gate-Drain Charge (Note 3)		Q _{gd}	--	7.0	--	
Input Capacitance	V _{DS} =75V, V _{GS} =0V, F=1.0MHz	C _{iss}	--	2230	--	pF
Output Capacitance		C _{oss}	--	293	--	
Reverse Transfer Capacitance		C _{rss}	--	22	--	
Switching						
Turn-On Delay Time (Note 3)	V _{DD} =50V, I _D =20A, V _{GS} =10V, R _G =6Ω	t _{d(on)}	--	13	--	nS
Rise Time (Note 3)		t _r	--	25	--	
Turn-Off Delay Time (Note 3)		t _{d(off)}	--	31	--	
Fall Time (Note 3)		t _f	--	26	--	
Source-Drain Diode Ratings and Characteristics (Note 2)						
Forward Voltage	V _{GS} =0V, I _F =10A	V _{SD}	--	0.7	1.2	V
Continuous Source Current	Integral reverse diode in the MOSFET	I _S	--	--	50	A
Pulsed Current (Note 1)		I _{SM}	--	--	200	A

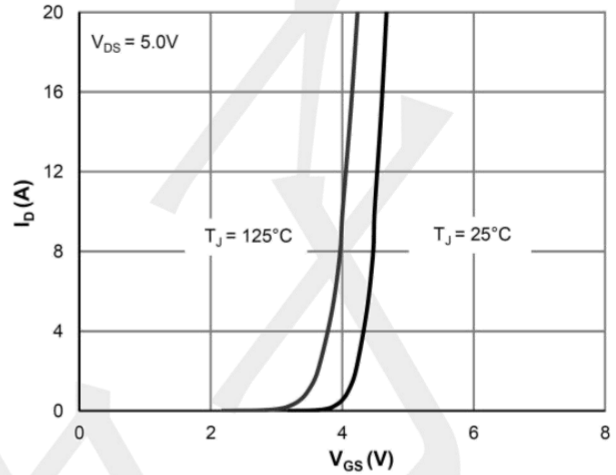
Notes:

1. Pulse test; pulse width ≤ 300 μS, duty cycle ≤ 2%.
2. Guaranteed by design, not subject to production testing.
3. Independent of operating temperature

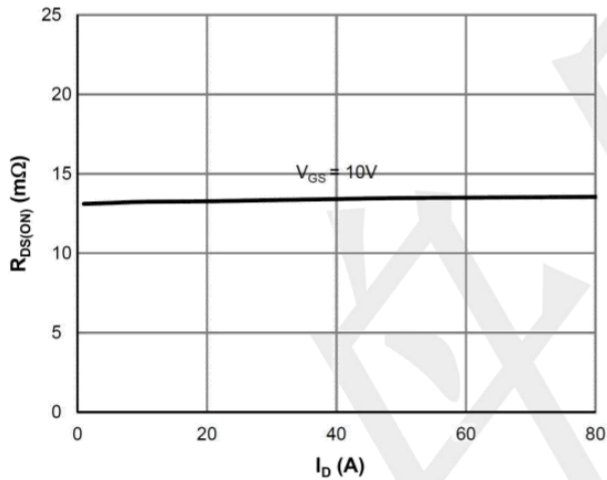
Typical Electrical and Thermal Characteristics



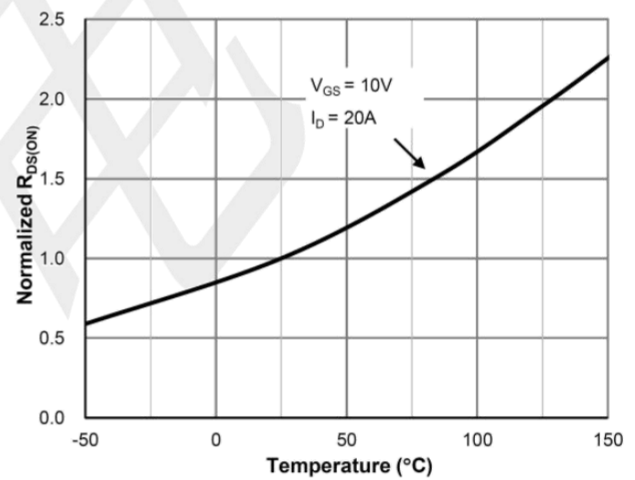
Saturation Characteristics



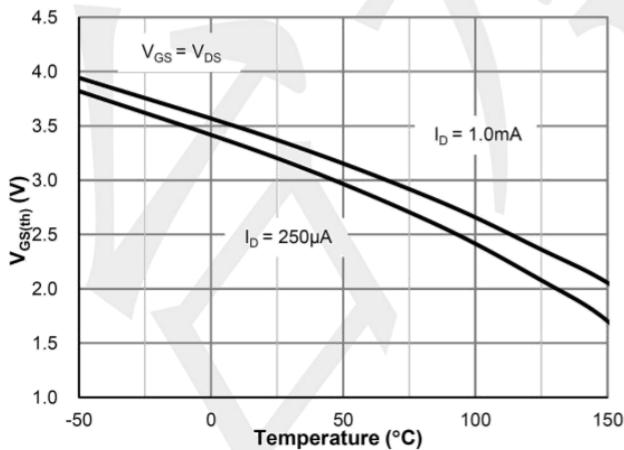
Transfer Characteristics



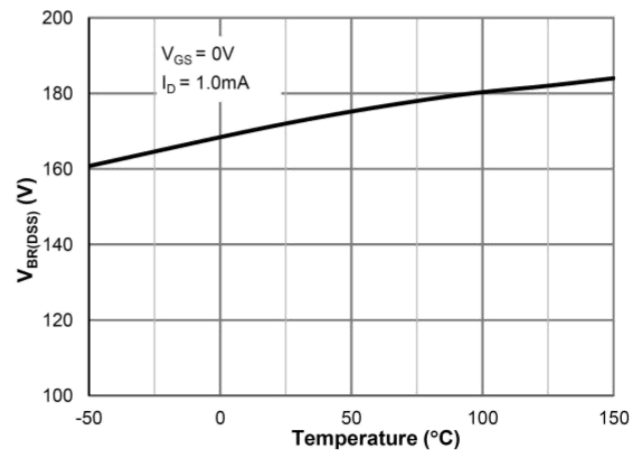
$R_{DS(ON)}$ vs. Drain Current



$R_{DS(ON)}$ vs. Junction Temperature

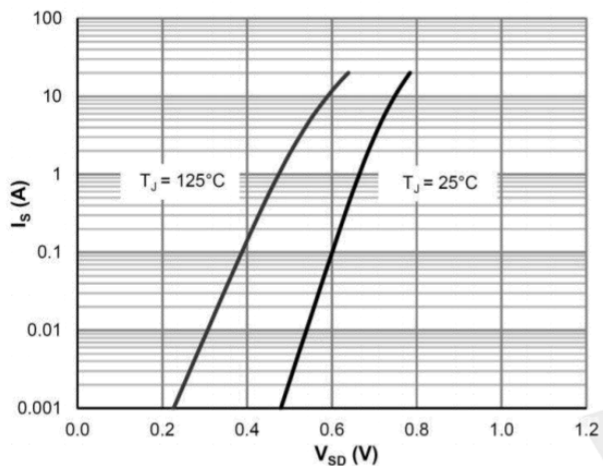


$V_{GS(th)}$ vs. Junction Temperature

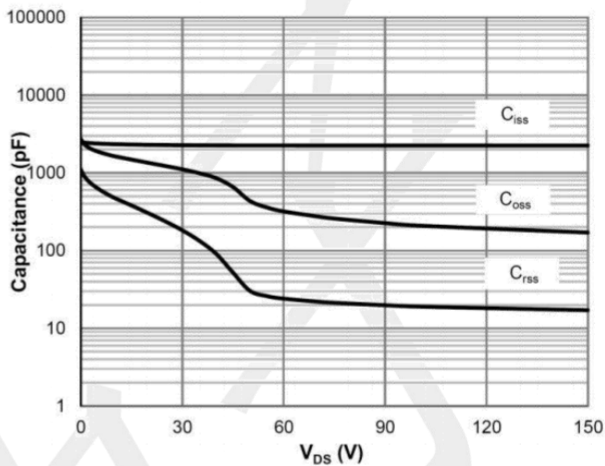


$V_{BR(DSS)}$ vs. Junction Temperature

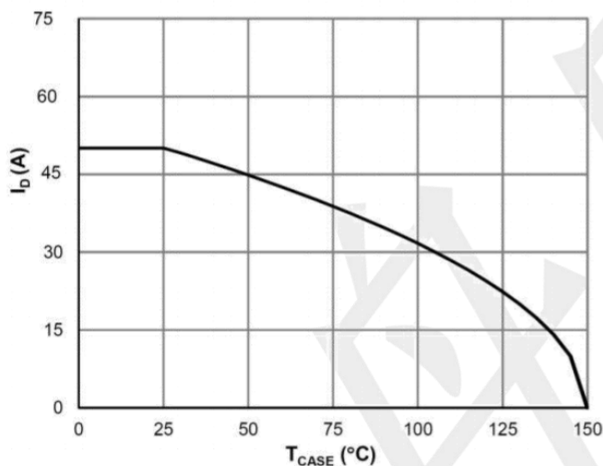
Typical Performance Characteristics



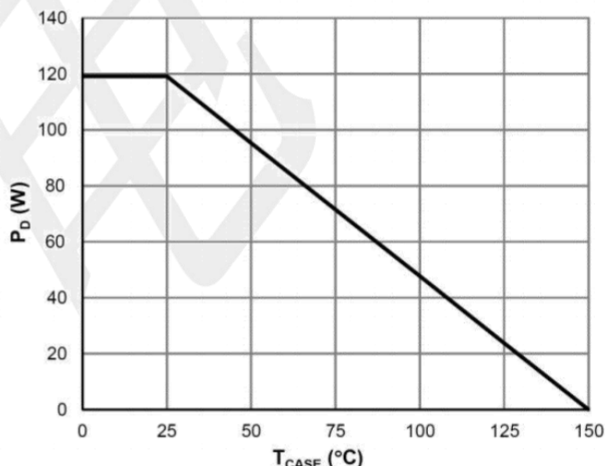
Body-Diode Characteristics



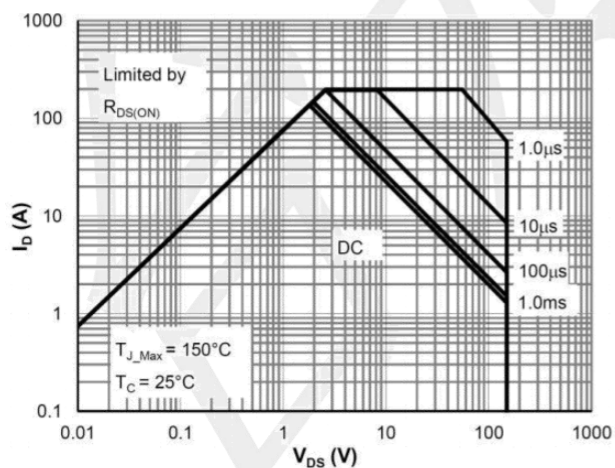
Capacitance Characteristics



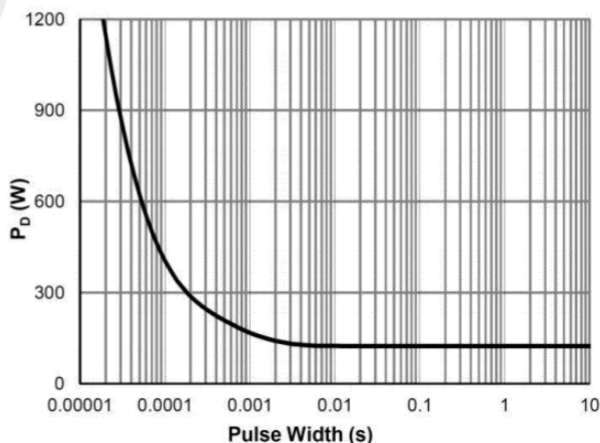
Current De-rating



Power De-rating



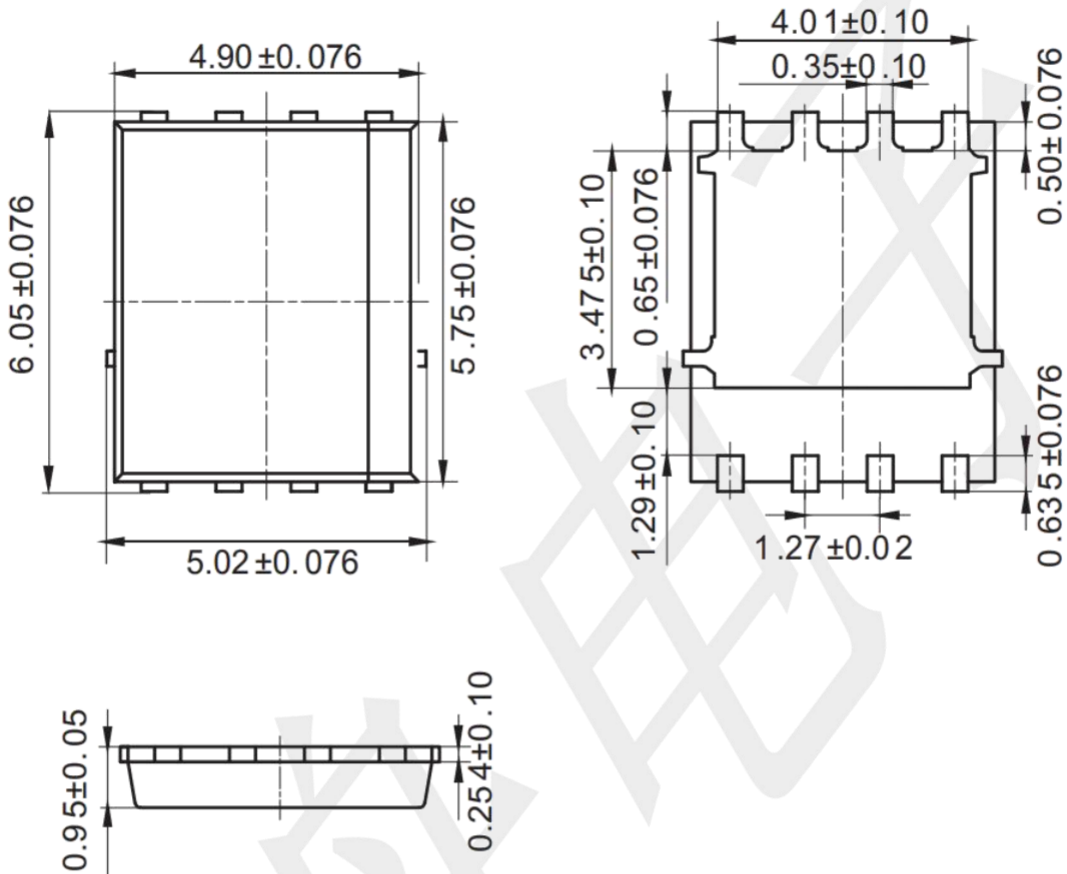
Maximum Safe Operating Area



Single Pulse Power Rating, Junction-to-Case

Package Information

PDFN5X6-8



Mounting Pad Layout (unit: mm)

